Photocouplers Infrared LED & Photo Transistor

TLP185(SE

1. Applications

- Office Equipment
- Programmable Logic Controllers (PLCs)
- AC Adapters
- I/O Interface Boards

2. General

The TLP185(SE consist of a photo transistor optically coupled to an infrared LED.
The TLP185(SE photocoupler is housed in the very small and thin SO6 package.
Since TLP185(SE is smaller than DIP package, it's suitable for high-density surface mounting application such as programmable controllers.

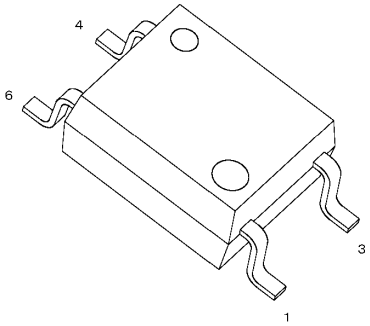
3. Features

(1) Collector-emitter voltage: 80 V (min)
(2) Current transfer ratio: 50% (min)
GB Rank: 100% (min)
(3) Isolation voltage: 3750 Vrms (min)
(4) Operating temperature: -55 to 110 °C
(5) Safety standards
UL-recognized: UL 1577, File No.E67349
cUL-recognized: CSA Component Acceptance Service No.5A File No.E67349
VDE-approved: EN IEC 60747-5-5, EN IEC 62368-1 **(Note 1)**
CQC-approved: GB4943.1 Japan and Thailand Factory

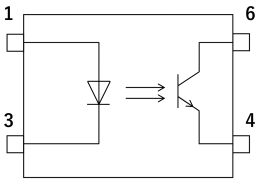
Can only be safely used in areas below 2000m above sea level.

Note 1: When a VDE approved type is needed, please designate the **Option (V4)**.

4. Packaging and Pin Assignment



11-4M1S



1: Anode
3: Cathode
4: Emitter
6: Collector

Start of commercial production
2013-01

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5. Principle of Operation

5.1. Mechanical Parameters

Characteristics	Min	Unit
Creepage distances	5.0	mm
Clearance	5.0	
Internal isolation thickness	0.4	

6. Absolute Maximum Ratings (Note) (Unless otherwise specified, T_a = 25 °C)

	Characteristics		Symbol	Note	Rating	Unit
LED	Input forward current		I_F		50	mA
	Input forward current derating	($T_a \geq$ 90 °C)	$\Delta I_F/\Delta T_a$		-1.5	mA/°C
	Input forward current (pulsed)		I_{FP}	(Note 1)	1	A
	Input reverse voltage		V_R		5	V
	Input power dissipation		P_D		100	mW
	Input power dissipation derating	($T_a \geq$ 90 °C)	$\Delta P_D/\Delta T_a$		-2.86	mW/°C
	Junction temperature		T_j		125	°C
Detector	Collector-emitter voltage		V_{CEO}		80	V
	Emitter-collector voltage		V_{ECO}		7	V
	Collector current		I_C		50	mA
	Collector power dissipation		P_C		150	mW
	Collector power dissipation derating	($T_a \geq$ 25 °C)	$\Delta P_C/\Delta T_a$		-1.5	mW/°C
	Junction temperature		T_j		125	°C
Common	Operating temperature		T_{opr}		-55 to 110	°C
	Storage temperature		T_{stg}		-55 to 125	
	Lead soldering temperature	(10 s)	T_{sol}		260	
	Total power dissipation		P_T		200	mW
	Isolation voltage	AC, 60 s, R.H. ≤ 60%	BV_S	(Note 2)	3750	Vrms

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Pulse width (PW) ≤ 100 μs, f = 100 Hz

Note 2: This device is considered as a two-terminal device: Pins 1 and 3 are shorted together, and pins 4 and 6 are shorted together.

7. Electrical Characteristics (Unless otherwise specified, T_a = 25 °C)

	Characteristics	Symbol	Note	Test Condition	Min	Typ.	Max	Unit
LED	Input forward voltage	V_F		I_F = 10 mA	1.1	1.25	1.4	V
	Input reverse current	I_R		V_R = 5 V	—	—	5	μA
	Input capacitance	C_t		V = 0 V, f = 1 MHz	—	30	—	pF
Detector	Collector-emitter breakdown voltage	$V_{(BR)CEO}$		I_C = 0.5 mA	80	—	—	V
	Emitter-collector breakdown voltage	$V_{(BR)ECO}$		I_E = 0.1 mA	7	—	—	
	Dark Current	I_{DARK}		V_{CE} = 48 V	—	0.001	0.08	μA
				V_{CE} = 48 V, T_a = 85 °C	—	1	50	
	Collector-emitter capacitance	C_{CE}		V = 0 V, f = 1 MHz	—	10	—	pF

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8. Coupled Electrical Characteristics (Unless otherwise specified, T_a = 25 °C)

Characteristics	Symbol	Note	Test Condition	Min	Typ.	Max	Unit
Current transfer ratio	I_C/I_F	(Note 1)	I_F = 5 mA, V_{CE} = 5 V, Blank Rank	50	—	600	%
			I_F = 5 mA, V_{CE} = 5 V, GB Rank	100	—	600	
Saturated current transfer ratio	$I_C/I_{F(sat)}$		I_F = 1 mA, V_{CE} = 0.4 V	—	60	—	
			I_F = 1 mA, V_{CE} = 0.4 V, (GR, GB, BL, GRL, GRH, BLL) Rank	30	—	—	
Collector-emitter saturation voltage	$V_{CE(sat)}$		I_C = 2.4 mA, I_F = 8 mA	—	—	0.3	V
			I_C = 0.2 mA, I_F = 1 mA	—	0.2	—	
			I_C = 0.2 mA, I_F = 1 mA, (GR, GB, BL, GRL, GRH, BLL) Rank	—	—	0.3	
OFF-state collector current	$I_{C(off)}$		V_F = 0.7 V, V_{CE} = 48 V	—	1	10	μA

Note 1: See Table 8.1 for current transfer ratio.

Table 8.1 Current Transfer Ratio (CTR) Rank (Note) (Unless otherwise specified, T_a = 25 °C)

Rank	Test Condition	Current transfer ratio I_C/I_F Min	Current transfer ratio I_C/I_F Max	Marking of Classification	Unit
Blank	I_F = 5 mA, V_{CE} = 5 V	50	600	Blank, YE, GR, GB, BL, Y+, G, G+, B	%
Y		50	150	YE	
GR		100	300	GR	
GB		100	600	GB	
BL		200	600	BL	
YH		75	150	Y+	
GRL		100	200	G	
GRH		150	300	G+	
BLL		200	400	B	

Note: Specify both the part number and a rank in this format when ordering.
Example: TLP185(GB,SE
For safety standard certification, however, specify the part number alone.
Example: TLP185(GB,SE: TLP185

9. Isolation Characteristics (Unless otherwise specified, T_a = 25 °C)

Characteristics	Symbol	Note	Test Condition	Min	Typ.	Max	Unit
Total capacitance (input to output)	C_S	(Note 1)	V_S = 0 V, f = 1 MHz	—	0.8	—	pF
Isolation resistance	R_S	(Note 1)	V_S = 500 V, R.H. ≤ 60%	10^{12}	10^{14}	—	Ω
Isolation voltage	BV_S	(Note 1)	AC, 60 s	3750	—	—	Vrms

Note 1: This device is considered as a two-terminal device: Pins 1 and 3 are shorted together, and pins 4 and 6 are shorted together.

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10. Switching Characteristics (Unless otherwise specified, T_a = 25 °C)

Characteristics	Symbol	Note	Test Condition	Min	Typ.	Max	Unit
Rise time	t_r		V_{CC} = 10 V, I_C = 2 mA, R_L = 100 Ω	—	2	—	μs
Fall time	t_f			—	3	—	
Turn-on time	t_{on}			—	3	—	
Turn-off time	t_{off}			—	3	—	
Turn-on time	t_{on}		See Fig. 10.1 V_{CC} = 5 V, I_F = 16 mA, R_L = 1.9 kΩ	—	0.5	—	
Storage time	t_s			—	25	—	
Turn-off time	t_{off}			—	40	—	

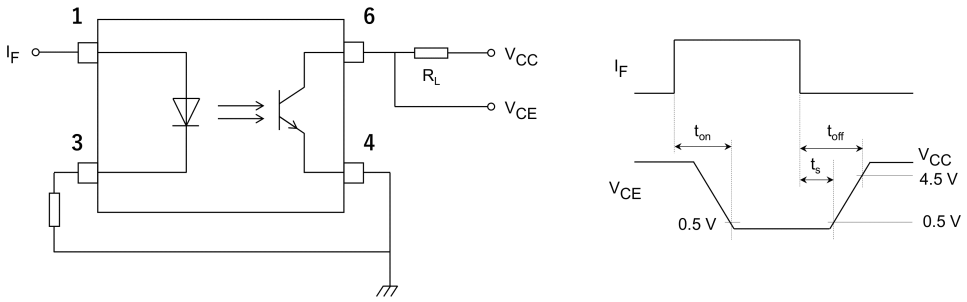


Fig. 10.1 Switching Time Test Circuit and Waveform

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11. Characteristics Curves (Note)

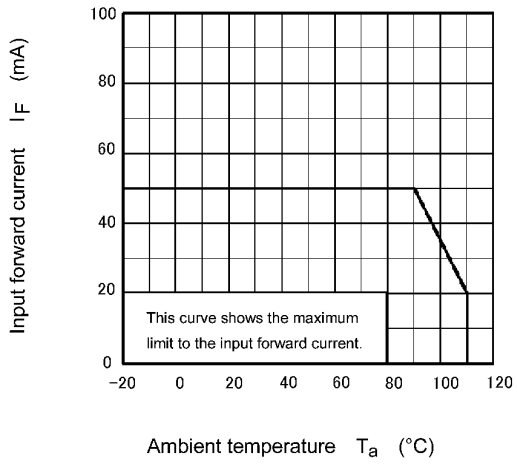


Fig. 11.1 I_F - T_a

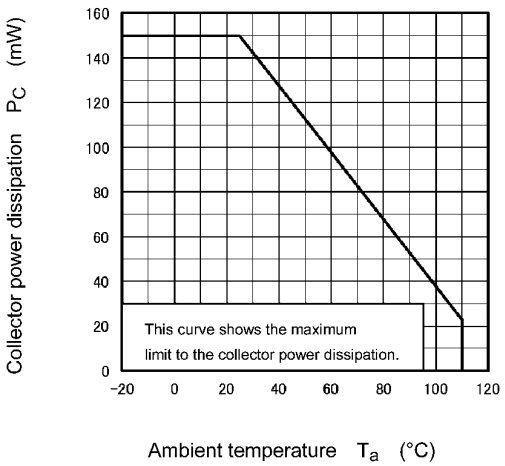


Fig. 11.2 P_C - T_a

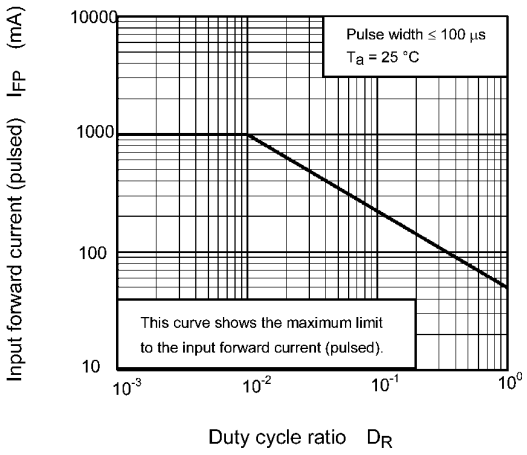


Fig. 11.3 I_{FP} - D_R

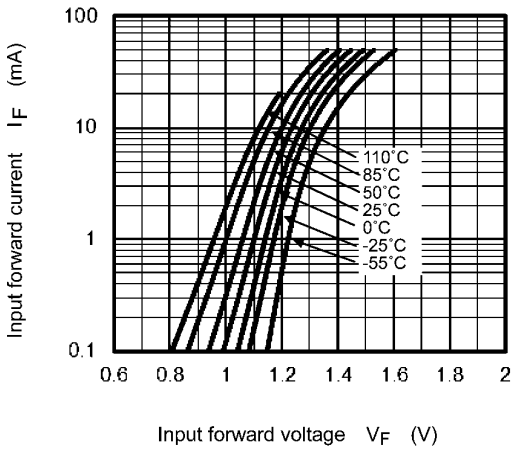


Fig. 11.4 I_F - V_F

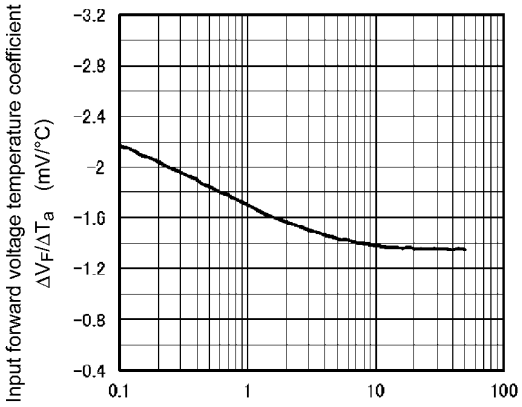


Fig. 11.5 $\Delta V_F/\Delta T_a$ - I_F

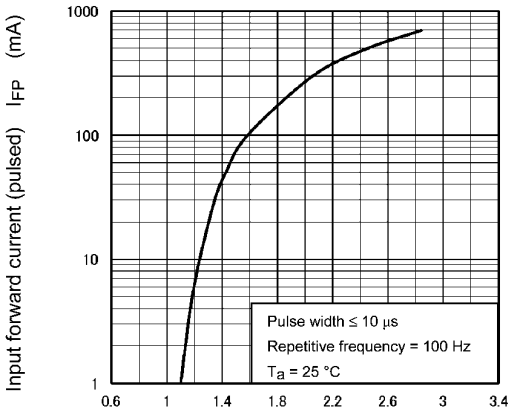


Fig. 11.6 I_{FP} - V_{FP}

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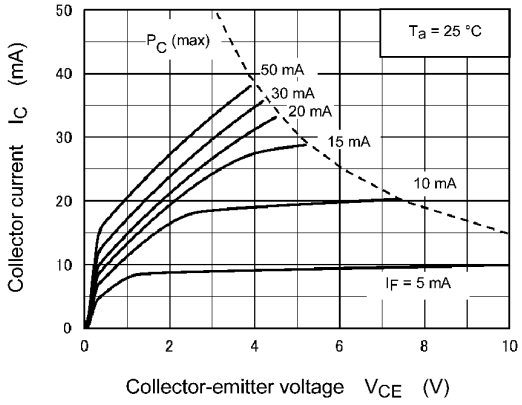


Fig. 11.7 I_C - V_{CE}

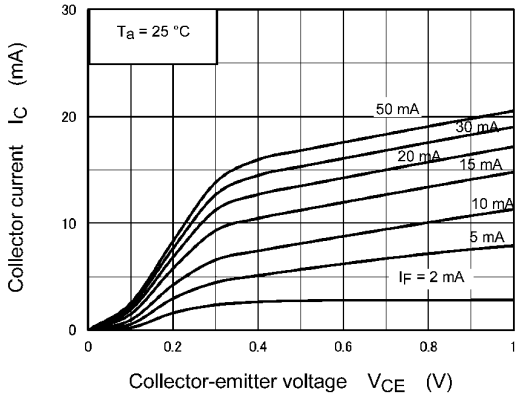


Fig. 11.8 I_C - V_{CE}

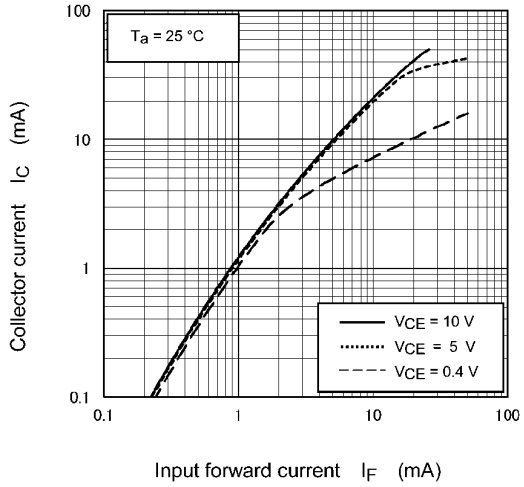


Fig. 11.9 I_C - I_F

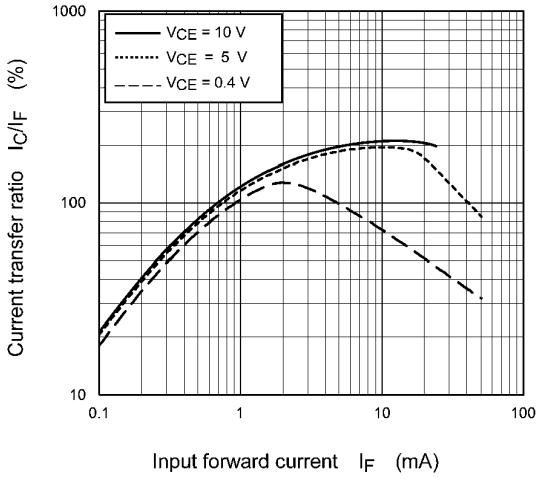


Fig. 11.10 I_C/I_F - I_F

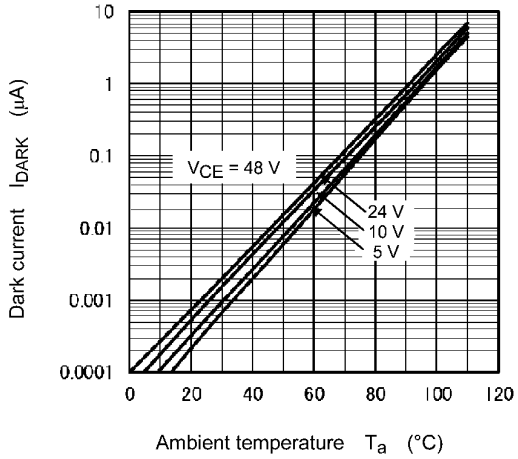


Fig. 11.11 I_{DARK} - T_a

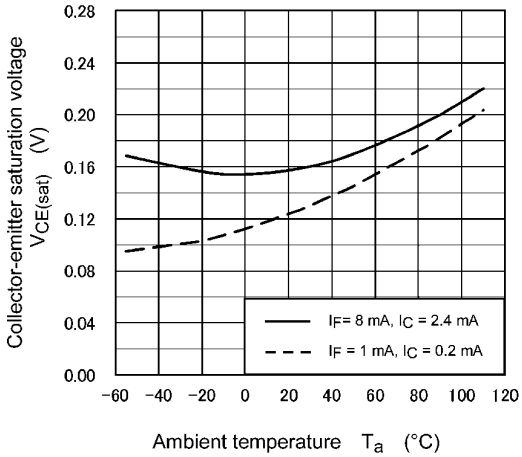


Fig. 11.12 $V_{CE(sat)}$ - T_a

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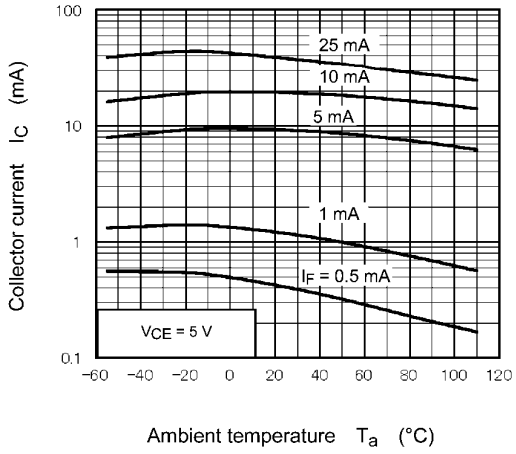


Fig. 11.13 I_C - T_a

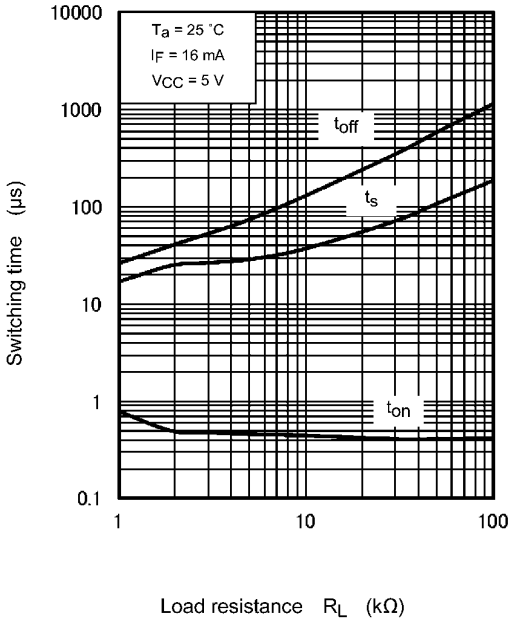


Fig. 11.14 Switching Time - R_L

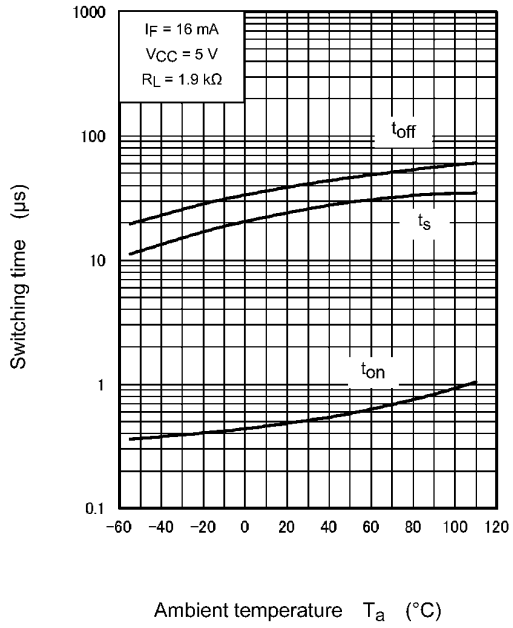


Fig. 11.15 Switching Time - T_a

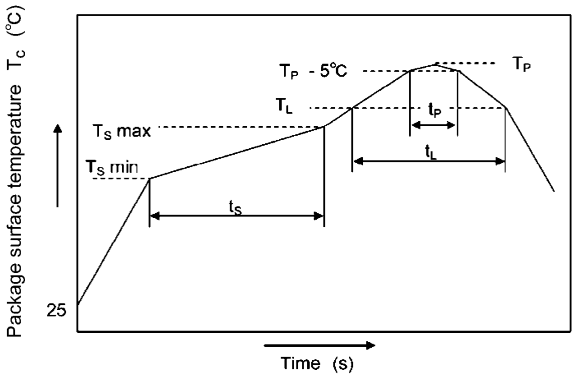
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

12. Soldering and Storage

12.1. Precautions for Soldering

The soldering temperature should be controlled as closely as possible to the conditions shown below, irrespective of whether a soldering iron or a reflow soldering method is used.

- When using soldering reflow.
  The soldering temperature profile is based on the package surface temperature.
  (See the figure shown below, which is based on the package surface temperature.)
  Reflow soldering must be performed once or twice.
  The mounting should be completed with the interval from the first to the last mountings being 2 weeks.



	Symbol	Min	Max	Unit
Preheat temperature	T_S	150	200	°C
Preheat time	t_S	60	120	s
Ramp-up rate (T_L to T_P)			3	°C/s
Liquidus temperature	T_L	217		°C
Time above T_L	t_L	60	150	s
Peak temperature	T_P		260	°C
Time during which T_c is between (T_P – 5) and T_P	t_P		30	s
Ramp-down rate (T_P to T_L)			6	°C/s

Fig. 12.1.1 An Example of a Temperature Profile When Lead(Pb)-Free Solder Is Used

- When using soldering flow
  Preheat the device at a temperature of 150 °C (package surface temperature) for 60 to 120 seconds.
  Mounting condition of 260 °C within 10 seconds is recommended.
  Flow soldering must be performed once.
- When using soldering Iron
  Complete soldering within 10 seconds for lead temperature not exceeding 260 °C or within 3 seconds not exceeding 350 °C
  Heating by soldering iron must be done only once per lead.

12.2. Precautions for General Storage

- Avoid storage locations where devices may be exposed to moisture or direct sunlight.
- Follow the precautions printed on the packing label of the device for transportation and storage.
- Keep the storage location temperature and humidity within a range of 5 °C to 35 °C and 45 % to 75 %, respectively.
- Do not store the devices in locations with poisonous gases (especially corrosive gases) or in dusty conditions.

- Store the devices in locations with minimal temperature fluctuations. Rapid temperature changes during storage can cause condensation, resulting in lead oxidation or corrosion, which will deteriorate the solderability of the leads.
- When restoring devices after removal from their packing, use anti-static containers.
- Do not allow loads to be applied directly to devices while they are in storage.

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13. Marking

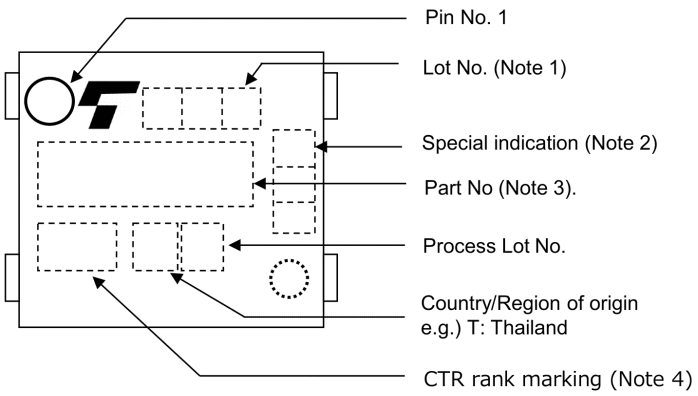


Fig. 13.1 Marking Example

Note 1: If the lot number is expressed with three characters, it indicates "manufacturing year (1 character) + manufacturing week (2 characters)".
For example, if the lot number shown on the product is "841", it means the product was manufactured in the 41st week of a year ending in 8.

Note 2: Special indication is put for the traceability enhancement.
Information of special indication
e.g. A01
A: Factory administration number
01: A counting of the number is started on every week from 01.
and reset when Lot No or weekly code is changed.

Note 3: P185 (Abbreviation code)

Note 4: For the CTR rank mark, please refer to the marking of classification in table 8.1 CTR rank table.

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14. EN IEC 60747-5-5 Option (V4) Specification

- Part number: TLP185 **(Note 1)**
- The following part naming conventions are used for the devices that have been qualified according to option (V4) of EN IEC 60747.

  Example: TLP185(V4GRTL,SE

  V4: EN IEC 60747 option
  GR: CTR rank
  TL: Tape type
  S: Domestic ID
  E: [[G]]/RoHS COMPATIBLE **(Note 2)**

Note 1: Use TOSHIBA standard type number for safety standard application.
e.g., TLP185(V4GRTL,SE → TLP185

Note 2: Please contact your Toshiba sales representative for details on environmental information such as the product's RoHS compatibility.
RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

Description	Symbol	Rating	Unit
Application classification for rated mains voltage ≤ 150 Vrms for rated mains voltage ≤ 300 Vrms		 I-IV I-III	—
Climatic classification		55 / 110 / 21	—
Pollution degree		2	—
Maximum operating insulation voltage	V_{IORM}	707	Vpeak
Input to output test voltage, Method A V_{pr} = 1.6 × V_{IORM}, type and sample test t_p = 10 s, partial discharge < 5 pC	V_{pr}	1131	Vpeak
Input to output test voltage, Method B V_{pr} = 1.875 × V_{IORM}, 100 % production test t_p = 1 s, partial discharge < 5 pC	V_{pr}	1330	Vpeak
Highest permissible overvoltage (transient overvoltage, t_{pr} = 60 s)	V_{TR}	6000	Vpeak
Safety limiting values (max. permissible ratings in case of fault, also refer to thermal derating curve) current (input current I_F, P_{so} = 0) power (output or total power dissipation) temperature	 I_{si} P_{so} T_s	 250 400 150	 mA mW °C
Insulation resistance V_{IO} = 500 V, T_a = 25 °C V_{IO} = 500 V, T_a = 100 °C V_{IO} = 500 V, T_a = T_s	R_{si}	≥ 10^{12} ≥ 10^{11} ≥ 10^9	Ω

Fig. 14.1 EN IEC 60747 Insulation Characteristics

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Minimum creepage distance	Cr	5.0 mm
Minimum clearance	Cl	5.0 mm
Minimum insulation thickness	ti	0.4 mm
Comparative tracking index	CTI	500

Fig. 14.2 Insulation Related Specifications (Note)

Note: This photocoupler is suitable for **safe electrical isolation** only within the safety limit data. Maintenance of the safety data shall be ensured by means of protective circuits.



Fig. 14.3 Marking on Packing for EN IEC 60747

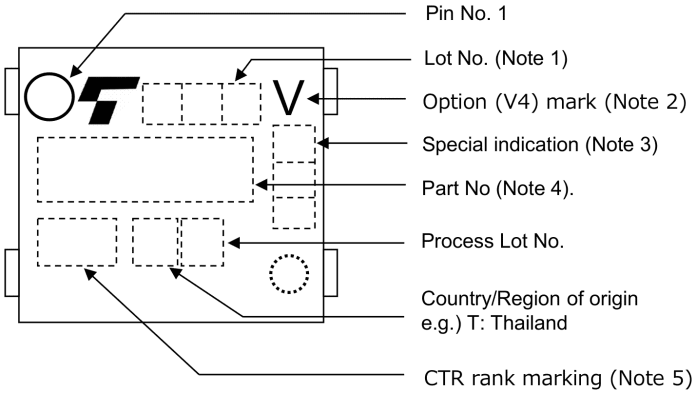


Fig. 14.4 Marking Example

Note 1: If the lot number is expressed with three characters, it indicates "manufacturing year (1 character) + manufacturing week (2 characters)".
For example, if the lot number shown on the product is "841", it means the product was manufactured in the 41st week of a year ending in 8.

Note 2: The above marking is applied to the photocouplers that have been qualified according to option (V4) of EN IEC 60747.

Note 3: Special indication is put for the traceability enhancement.
Information of special indication
e.g. A01
A: Factory administration number
01: A counting of the number is started on every week from 01.
and reset when Lot No or weekly code is changed.

Note 4: P185 (Abbreviation code)

Note 5: For the CTR rank mark, please refer to the marking of classification in table 8.1 CTR rank table.

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Figure 1 Partial discharge measurement procedure according to EN IEC 60747
Destructive test for qualification and sampling tests.

Method A

(for type and sampling tests, destructive tests)

t_1, t_2	= 1 to 10 s
t_3, t_4	= 1 s
t_p (Measuring time for partial discharge)	= 10 s
t_b	= 12 s
t_{ini}	= 60 s

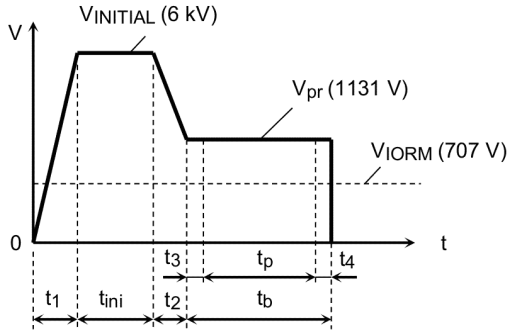


Figure 2 Partial discharge measurement procedure according to EN IEC 60747
Non-destructive test for 100 % inspection.

Method B

(for sample test, non-destructive test)

t_3, t_4	= 0.1 s
t_p (Measuring time for partial discharge)	= 1 s
t_b	= 1.2 s

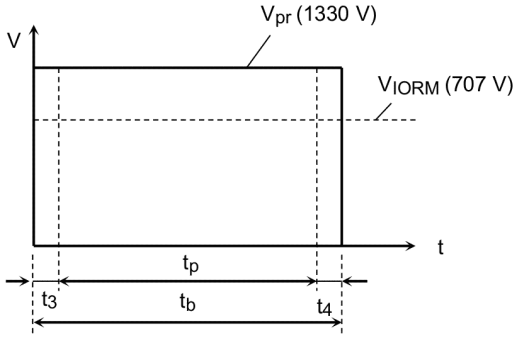


Figure 3 Dependency of maximum safety ratings on ambient temperature

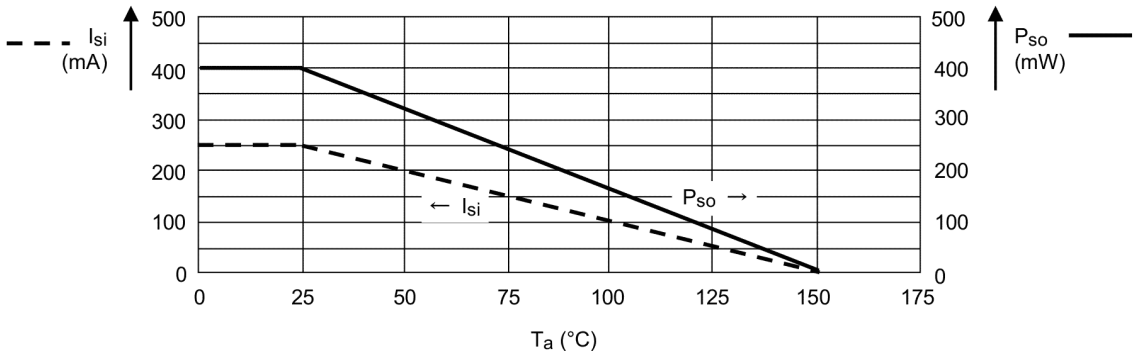
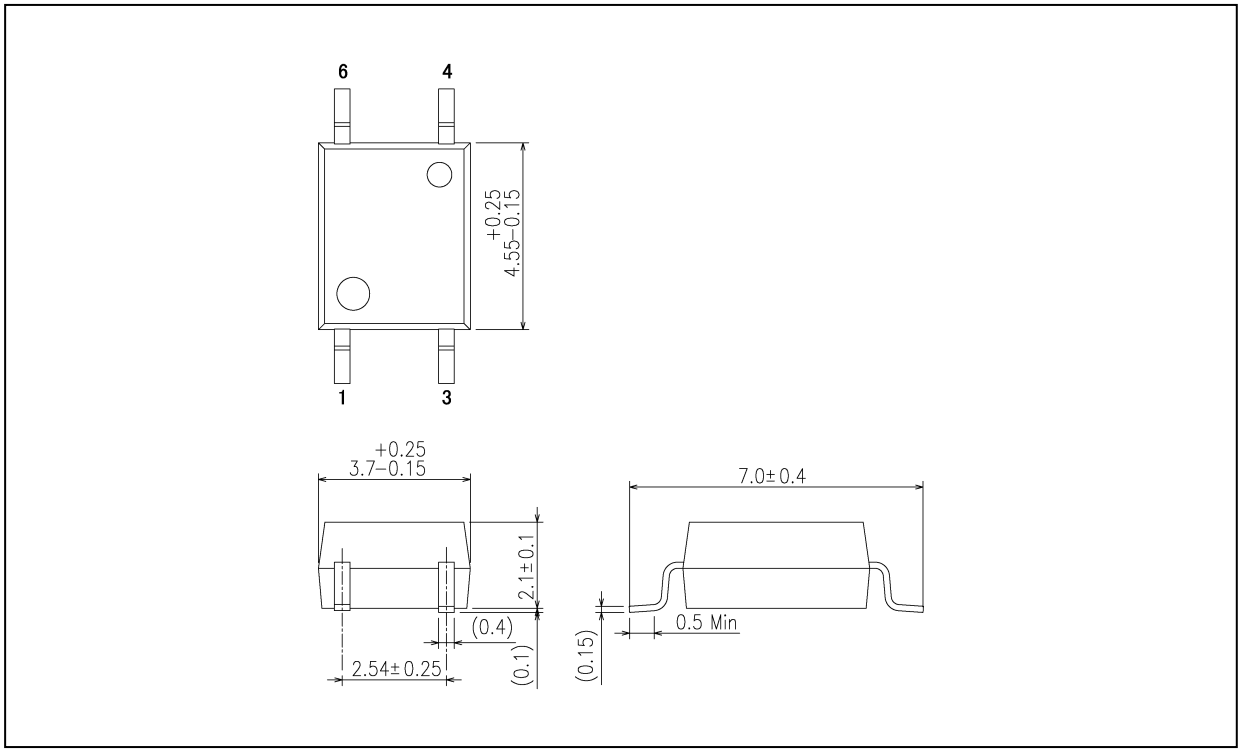


Fig. 14.5 Measurement Procedure

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Package Dimensions

Unit: mm



Weight: 0.08 g (typ.)

Package Name(s)
TOSHIBA: 11-4M1S

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